

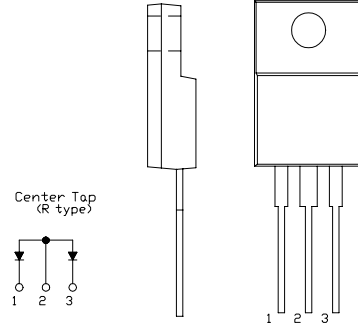
10A 60V

SBD Type : **FRQ10A06**

OUTLINE DRAWING

構造 : ショットキーバリアダイオード(SBD)
Construction: Schottky barrier Diode
アノード コモン型

用途 : 高周波整流用
Application : High Frequency Rectification



最大定格 / Maximum Ratings

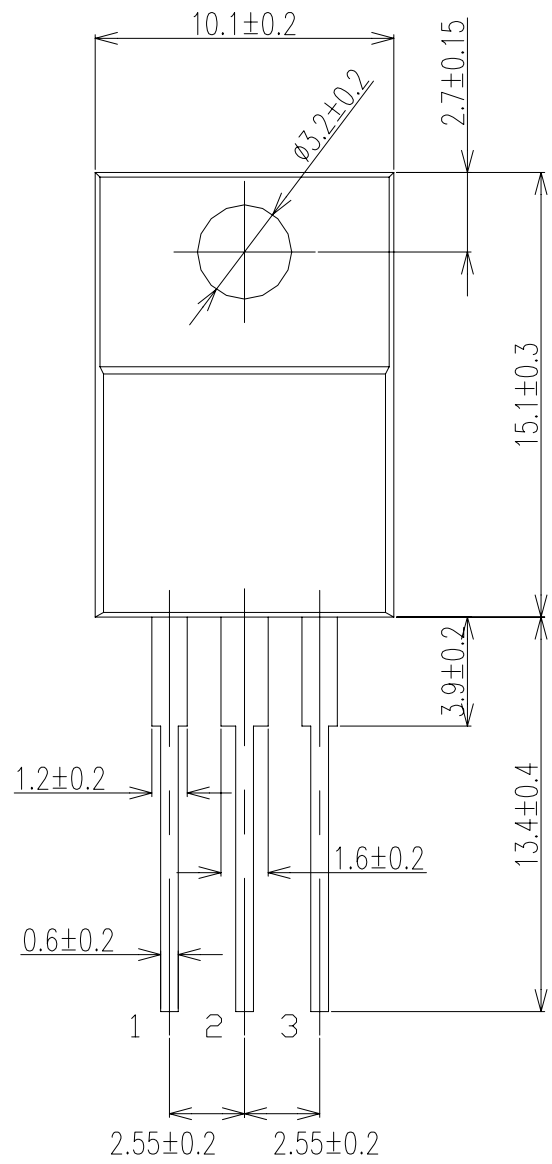
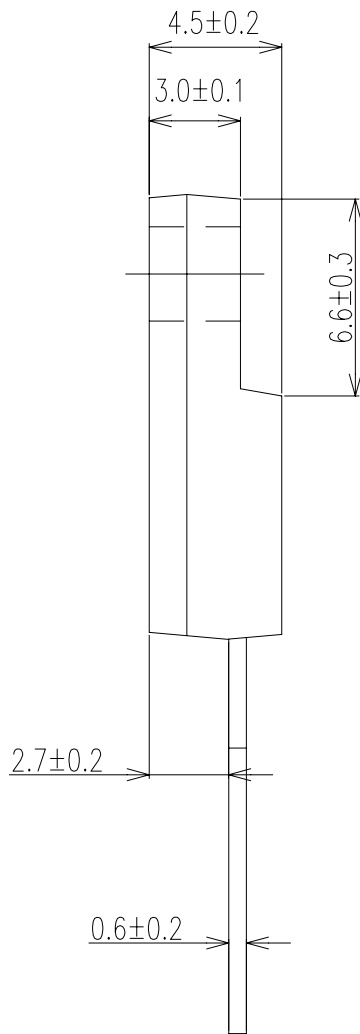
Approx Net Weight:1.75g

Rating	Symbol	FRQ10A06		Unit
くり返しピーク逆電圧 Repetitive Peak Reverse Voltage	V_{RRM}	60		V
非くり返しピーク逆電圧 Non-repetitive Peak Reverse voltage	V_{RSM}	65		V
平均整流電流 Average Rectified Output Current	I_0	10	$T_c=108$ 50 Hz, 正弦全波通電、抵抗負荷 Full Sine Wave Resistive Load	A
実効順電流 RMS Forward Current	$I_{F(RMS)}$	11.1		A
サージ順電流 Surge Forward Current	I_{FSM}	110	50 Hz 正弦全波, 1サイクル, 非くり返し Full Sine Wave, 1cycle, Non-repetitive	A
動作接合温度範囲 Operating Junction Temperature Range	T_{jw}	- 40 ~ + 150		
保存温度範囲 Storage Temperature Range	T_{stg}	- 40 ~ + 150		
締め付けトルク Mounting torque	F_{tor}	0.5	推奨値 Recommended value	N·m

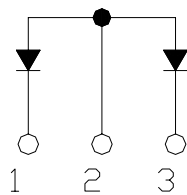
電氣的・熱的特性 / Electrical · Thermal Characteristics

Characteristics	Symbol	Conditions	Min	Typ	Max.	Unit
ピーク逆電流 Peak Reverse Current	I_{RM}	$T_j=25$, $V_{RM}=V_{RRM}$ per Diode	-	-	5	mA
ピーク順電圧 Peak Forward Voltage	V_{FM}	$T_j=25$, $I_{FM}= 5A$ per Diode	-	-	0.58	V
熱抵抗 Thermal Resistance	$R_{th(j-c)}$	接合部・ケース間 Junction to Case	-	-	3	/W
	$R_{th(c-f)}$	ケース・フィン間 Case to Fin	-	-	1.5	

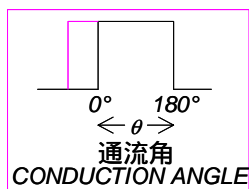
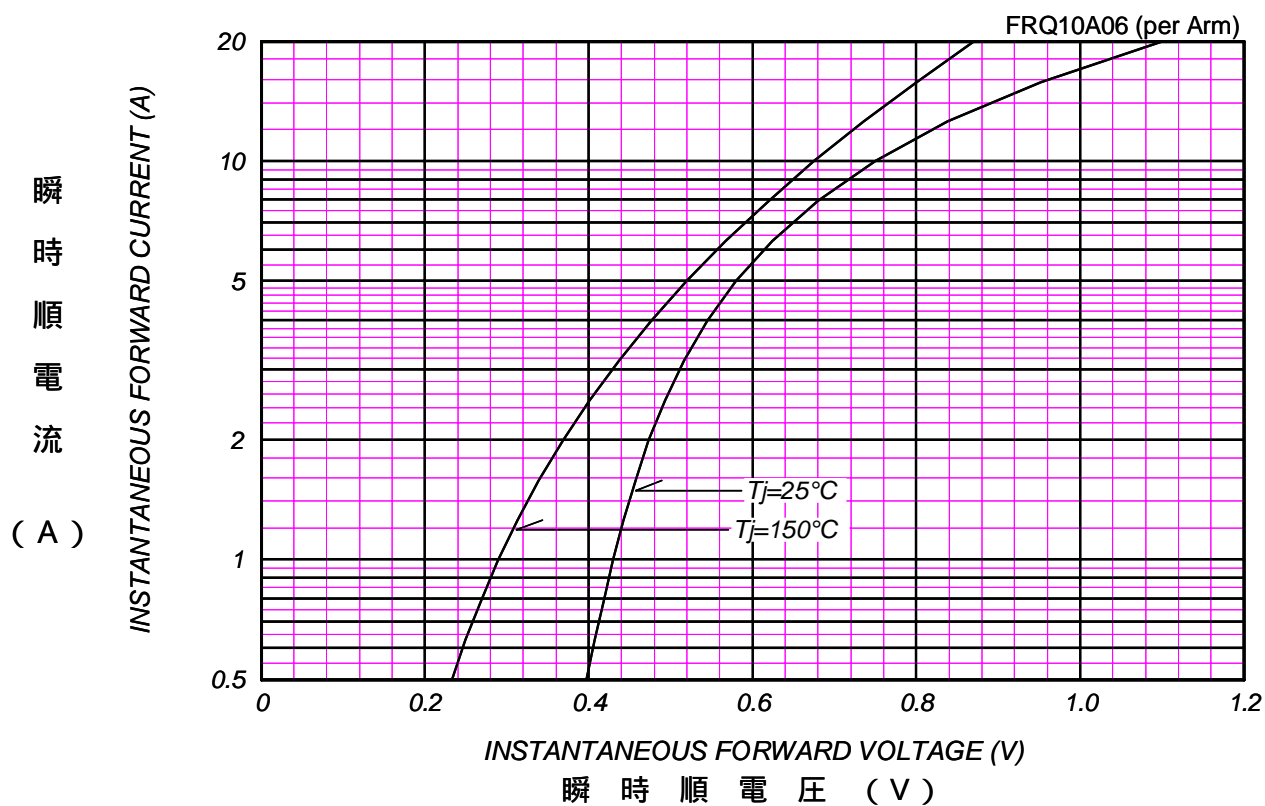
FRQ_A_外形図 (mm)



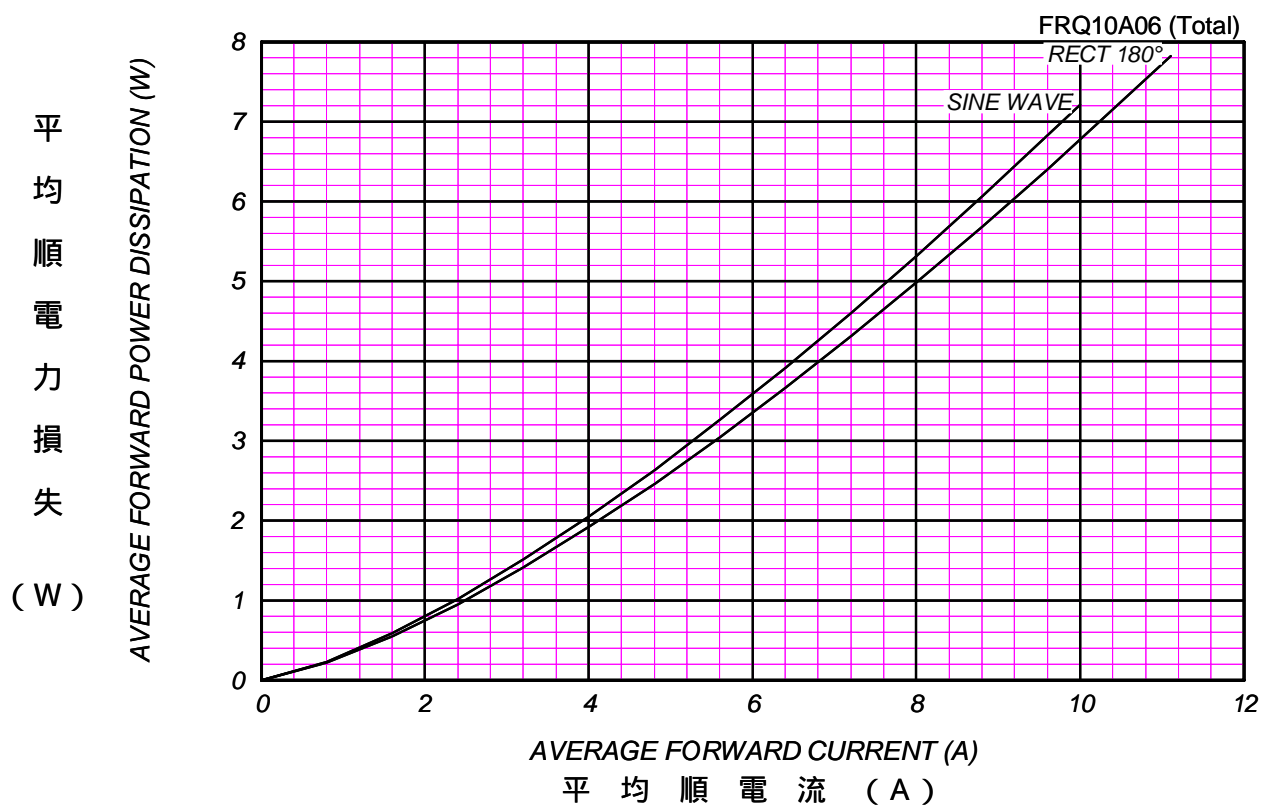
Center Tap
(R type)



順電壓特性
FORWARD CURRENT VS. VOLTAGE

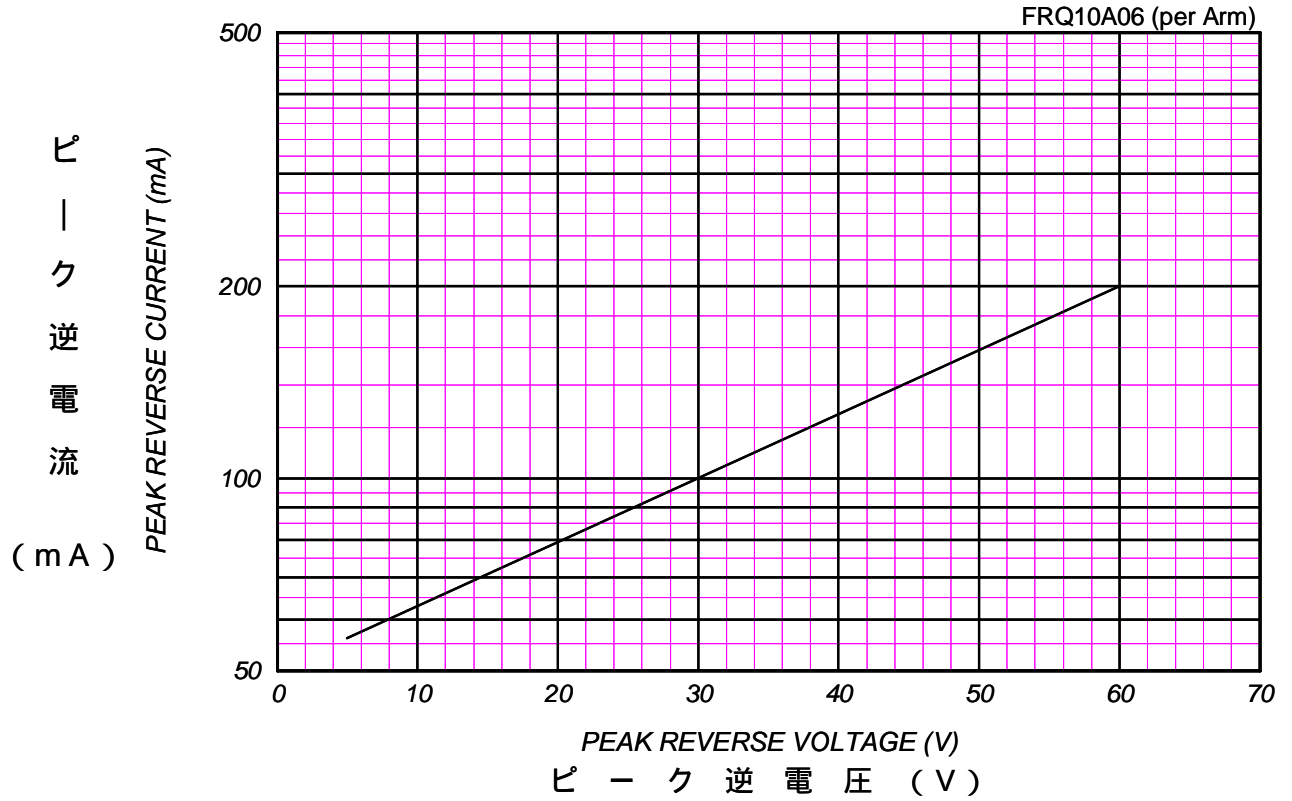


平均順電力損失特性
AVERAGE FORWARD POWER DISSIPATION

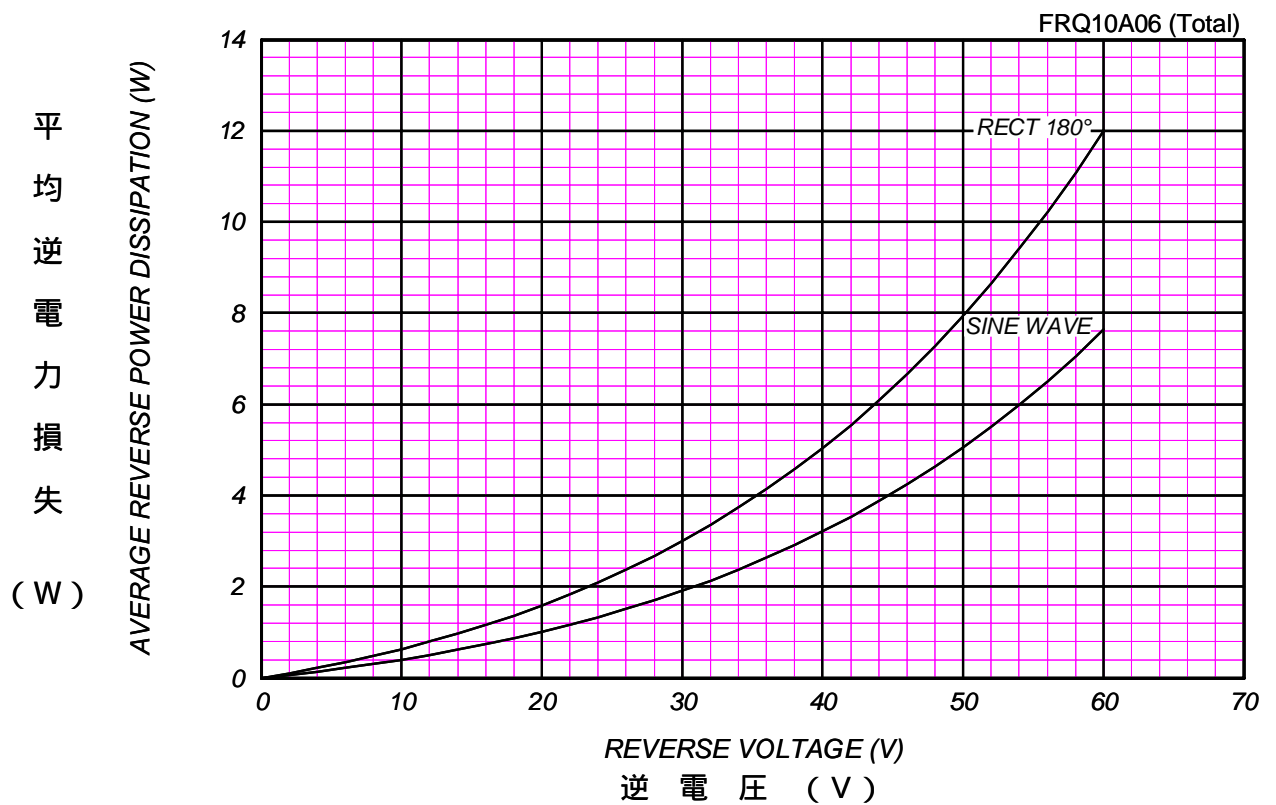


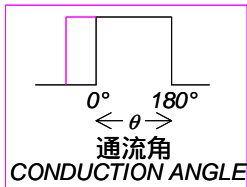
ピーク逆電流 - ピーク逆電圧特性
 PEAK REVERSE CURRENT VS. PEAK REVERSE VOLTAGE

T_j = 150 °C



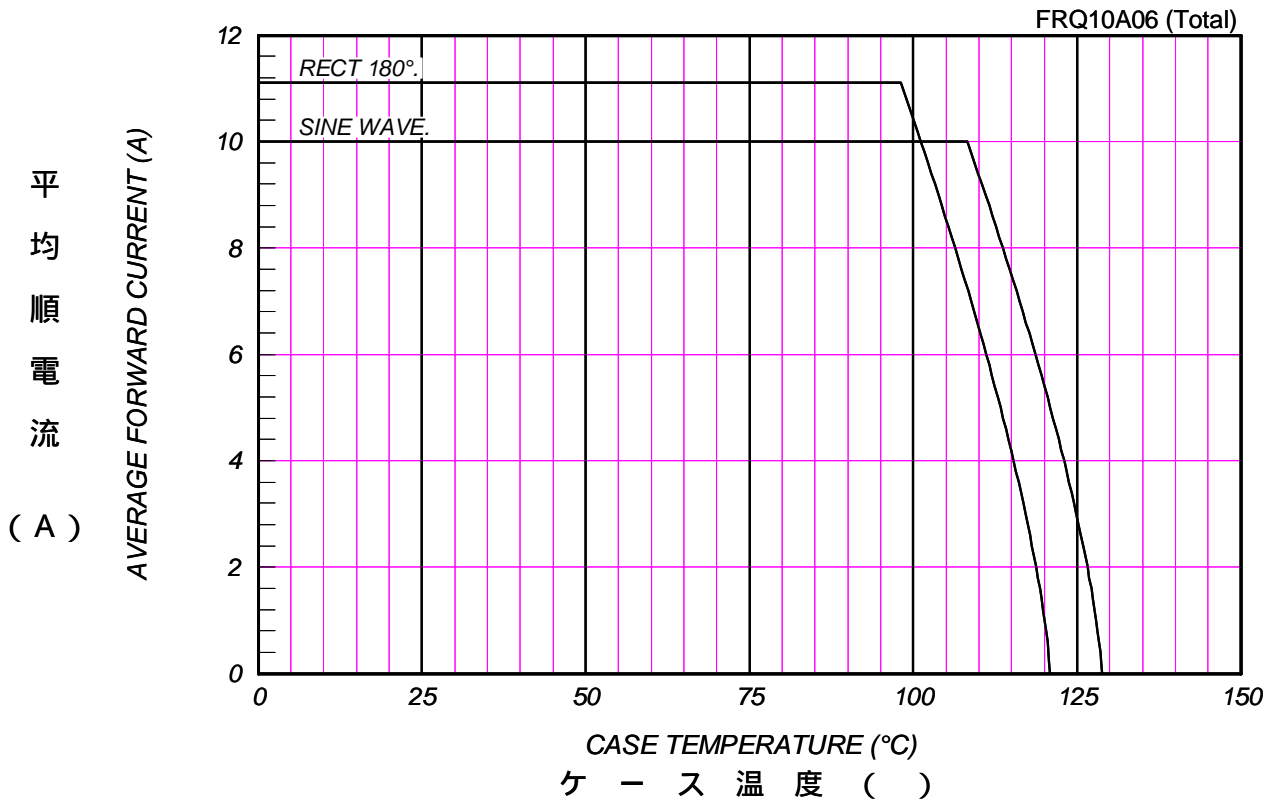
平均逆電力損失
 AVERAGE REVERSE POWER DISSIPATION





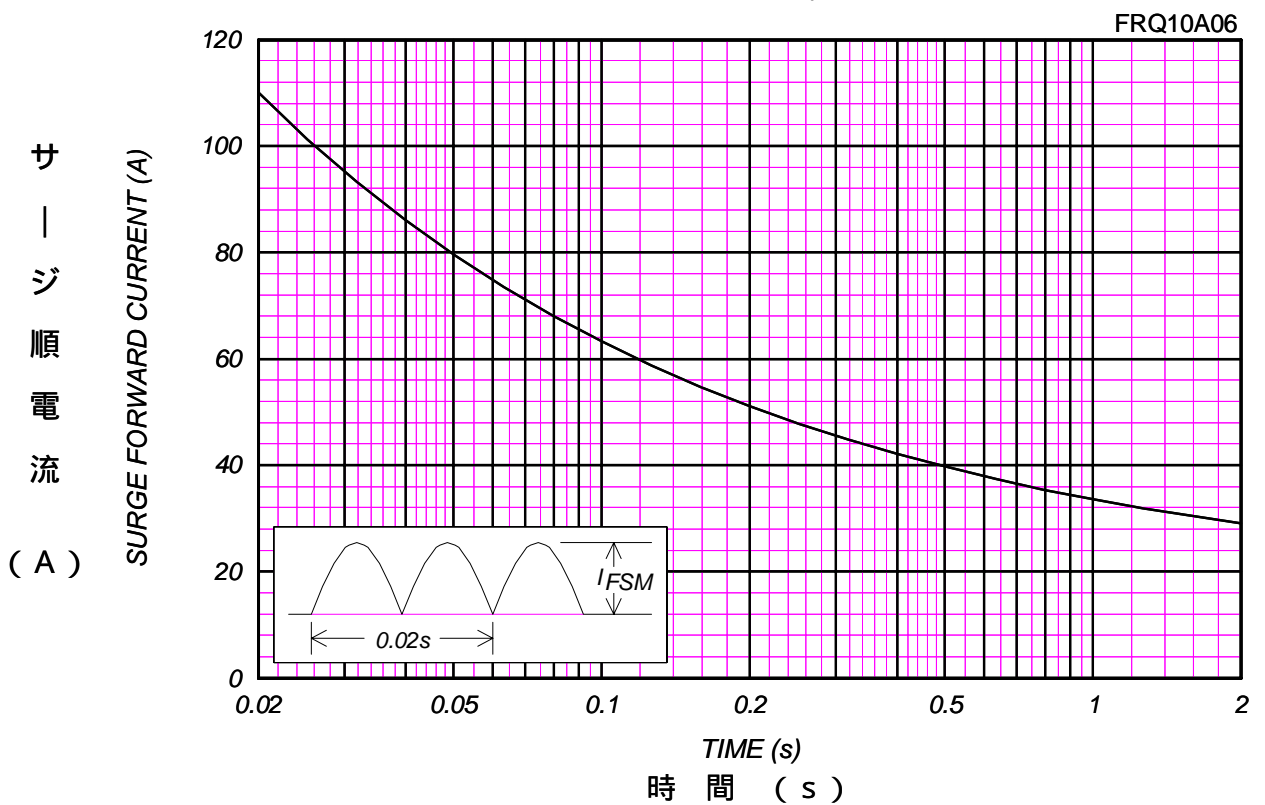
平均順電流 - ケース温度定格
AVERAGE FORWARD CURRENT VS. CASE TEMPERATURE

$V_{RM}=60V$



サージ順電流定格
SURGE CURRENT RATINGS

f=50Hz, Sine Wave, Non-Repetitive, No Load



接 合 容 量 特 性
JUNCTION CAPACITANCE VS. REVERSE VOLTAGE

$T_j=25^{\circ}\text{C}$, $V_m=20mV_{\text{RMS}}$, $f=100\text{kHz}$, Typical Value

FRQ10A06 (per Arm)

